



N-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|-----------------------------------|--------------------|-----------------------|--|--|
| V _{DS} (V) | $R_{DS(on)}(\Omega)$ | I _D (A) | Q _g (Typ.) | | |
| 30 | 0.020 at V _{GS} = 10 V | 12 ^a | 4.7 nC | | |
| 30 | 0.027 at $V_{GS} = 4.5 \text{ V}$ | 10.4 | 7.7 110 | | |

SO-8 S 1 8 D S 2 7 D S 3 6 D G 4 5 D

Ordering Information: Si4176DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

Top View

FEATURES

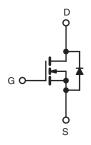
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Load Switch
- Low Current dc-to-dc
- Notebook



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATIN | IGS $T_A = 25 ^{\circ}C$, | unless other | erwise noted | |
|---|-----------------------------|-----------------------------------|---------------------|----|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V_{DS} | 30 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | v | |
| | T _C = 25 °C | | 12 ^a | |
| Continuous Drain Current (T _{.I} = 150 °C) | T _C = 70 °C | Ī _{I-} | 9.7 | |
| Continuous Brain Current (1) = 130 C) | T _A = 25 °C | l _D | 8.3 ^{b, c} | |
| | T _A = 70 °C | 1 1 | 6.6 ^{b, c} | Α |
| Pulsed Drain Current | | I _{DM} | 40 | ^ |
| Continuous Source-Drain Diode Current | T _C = 25 °C | I _S | 4.2 | |
| Continuous Source-Diam Blode Guirent | T _A = 25 °C | | 2 ^{b, c} | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 10 | |
| Single Pulse Avalanche Energy | | E _{AS} | 5 | mJ |
| | T _C = 25 °C | P _D | 5 | |
| Maximum Power Dissipation | T _C = 70 °C | | 3.2 | w |
| Maximum Fower Dissipation | T _A = 25 °C | | 2.4 ^{b, c} | v |
| | T _A = 70 °C | 1 | 1.5 ^{b, c} | |
| Operating Junction and Storage Temperature | e Range | T _J , T _{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | | |
|---|--------------|------------|---------|------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | | |
| Maximum Junction-to-Ambient ^{b, d} | t ≤ 10 s | R_{thJA} | 42 | 53 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R_{thJF} | 19 | 25 | 0/11 | |

Notes:

- a. Package Limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s
- d. Maximum under Steady State conditions is 85 °C/W.

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| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit | |
|---|-------------------------|--|------|-----------|-------|-------|--|
| Static | | | | 1 - 7 - | 1 | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$ | 30 | | | V | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | | | 28 | | mV/°C | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = 250 μA | | - 5.5 | | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$ | 1.2 | | 2.2 | V | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA | |
| | | V _{DS} = 30 V, V _{GS} = 0 V | | | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C | | | 10 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 20 | | | Α | |
| | , , | $V_{GS} = 10 \text{ V}, I_D = 8.3 \text{ A}$ | | 0.016 | 0.020 | | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 7.2 A | | 0.022 | 0.027 | Ω | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 15 V, I _D = 8.3 A | | 23 | | S | |
| Dynamic ^b | | 20 2 | | L | l | | |
| Input Capacitance | C _{iss} | | | 490 | | | |
| Output Capacitance | C _{oss} | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | | 110 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 61 | | | |
| | | $V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 8.3 \text{ A}$ | | 9.6 | 15 | nC | |
| Total Gate Charge | Q_g | | | 4.7 | 7.1 | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 8.3 \text{ A}$ | | 1.65 | | | |
| Gate-Drain Charge | Q_{gd} | | | 1.75 | | | |
| Gate Resistance | R_{g} | f = 1 MHz | 0.5 | 2.6 | 5.2 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 15 | 25 | | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 2.2 Ω | | 15 | 25 | 1 | |
| Turn-Off Delay Time | t _{d(off)} | $I_D\cong 6.7$ A, $V_{GEN}=4.5$ V, $R_g=1$ Ω | | 13 | 20 | | |
| Fall Time | t _f | | | 10 | 15 | 1 | |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 15 | ns | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 2.2 Ω | | 10 | 15 | | |
| Turn-Off Delay Time | t _{d(off)} | $\text{I}_\text{D}\cong 6.7~\text{A},~\text{V}_\text{GEN}$ = 10 V, R_g = 1 Ω | | 15 | 25 | | |
| Fall Time | t _f | | | 10 | 15 | | |
| Drain-Source Body Diode Characteristi | cs | | I. | | • | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 4.2 | ۸ | |
| Pulse Diode Forward Current | I _{SM} | | | | 40 | Α | |
| Body Diode Voltage | V_{SD} | $I_S = 6.7 \text{ A}, V_{GS} = 0 \text{ V}$ | | 0.8 | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | | | 15 | 30 | ns | |
| Body Diode Reverse Recovery Charge | Q _{rr} | L = 6.7 A dl/dt = 100 A/vo T = 25.00 | | 8 | 16 | nC | |
| Reverse Recovery Fall Time | t _a | $I_F = 6.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$ | | 8.5 | | | |
| Reverse Recovery Rise Time | t _b | \dashv | | 6.5 | İ | ns | |

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %

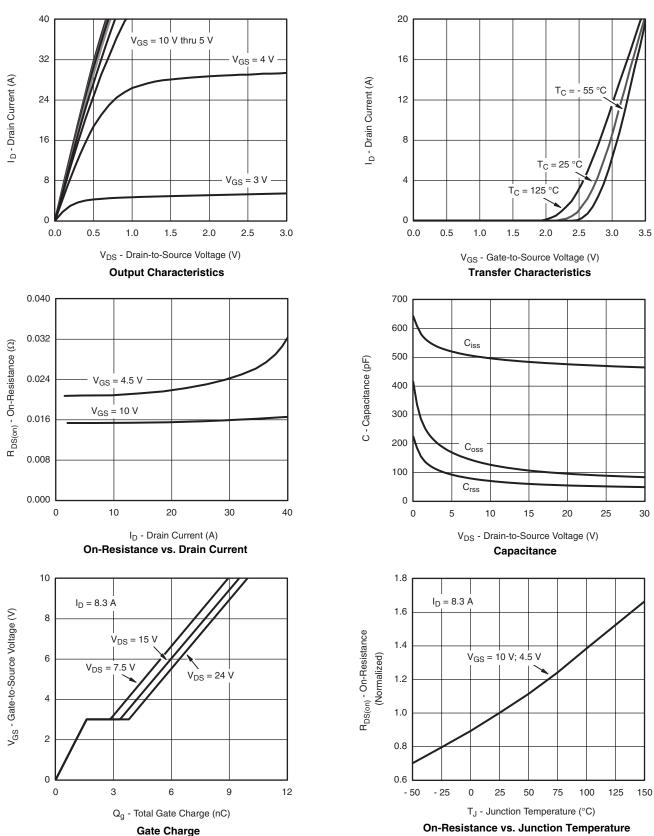
b. Guaranteed by design, not subject to production testing.







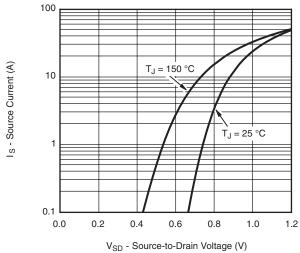
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



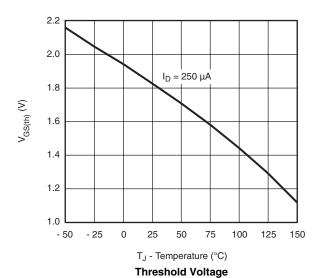
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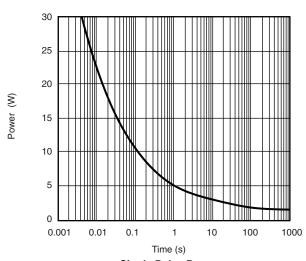
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

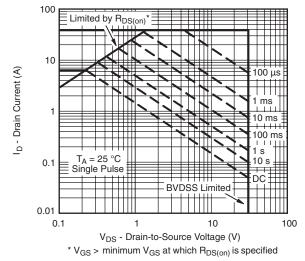


Source-Drain Diode Forward Voltage





Single Pulse Power

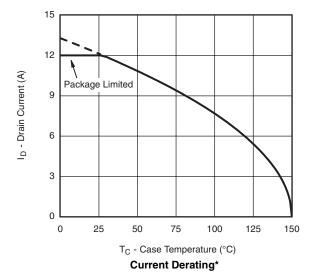


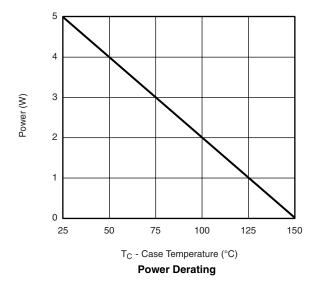




Si4176DY Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



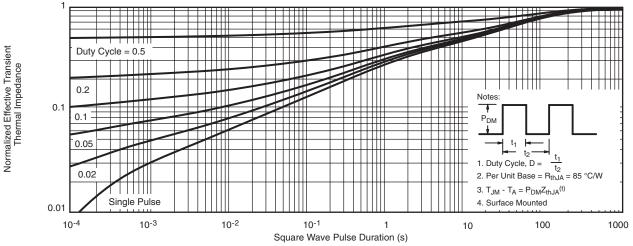


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

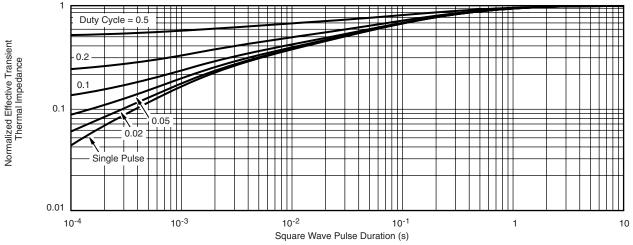
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



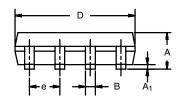
Normalized Thermal Transient Impedance, Junction-to-Foot

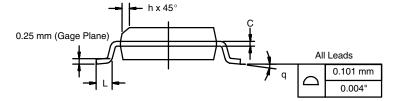
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







| | MILLIM | IETERS | INC | INCHES | | |
|--------------------------------|--------|--------|--------|-----------|--|--|
| DIM | Min | Max | Min | Max | | |
| Α | 1.35 | 1.75 | 0.053 | 0.069 | | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | | |
| Е | 3.80 | 4.00 | 0.150 | 0.157 | | |
| е | 1.27 | BSC | 0.050 | 0.050 BSC | | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | | |
| q | 0° | 8° | 0° | 8° | | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | | |
| ECN: C-06527-Rev. I. 11-Sep-06 | | | | | | |

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APPLICATION NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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